

Title (en)

METHOD FOR THE PRODUCTION OF A SINGLE-CRYSTAL FILM, IN PARTICULAR PIEZOELECTRIC

Title (de)

VERFAHREN ZUR HERSTELLUNG EINER EINKRISTALLSCHICHT, INSBESONDERE EINER PIEZOELEKTRISCHEN SCHICHT

Title (fr)

PROCEDE DE FABRICATION D'UNE COUCHE MONOCRISTALLINE, NOTAMMENT PIEZOELECTRIQUE

Publication

EP 3394324 A1 20181031 (FR)

Application

EP 16819558 A 20161221

Priority

- FR 1563055 A 20151222
- EP 2016082245 W 20161221

Abstract (en)

[origin: WO2017108994A1] The invention relates to a method for the production of a single-crystal film (10), characterised in that it comprises the following successive steps: the provision of a donor substrate (100) comprising a piezoelectric material of composition ABO₃, wherein A consists of at least one element from among Li, Na, K, H, Ca, and B consists of at least one element from among Nb, Ta, Sb, V; the provision of a receiver substrate (110); the transfer of a so-called "seed layer" from the donor substrate (100) to the receiver substrate (110), by means of bonding the donor substrate to the receiver substrate such that the seed layer (102) is located at the bonding interface, and the subsequent thinning of the donor substrate (100) as far as the seed layer (102); the epitaxial growth of a single-crystal film (103) on the piezoelectric material ABO₃ of the seed layer (102), said film having composition A'B'O₃, wherein: A' consists of at least one element from among Li, Na, K, H; B' consists of at least one element from among Nb, Ta, Sb, V; and A' is different from A or B' is different from B.

IPC 8 full level

C30B 25/18 (2006.01); **H10N 30/093** (2023.01); **C30B 29/22** (2006.01); **H01L 21/762** (2006.01); **H10N 30/072** (2023.01); **H10N 30/076** (2023.01); **H10N 30/079** (2023.01); **H10N 30/20** (2023.01); **H10N 30/853** (2023.01); **H10N 30/87** (2023.01)

CPC (source: EP KR US)

C30B 25/186 (2013.01 - EP KR US); **C30B 29/22** (2013.01 - EP KR US); **C30B 29/30** (2013.01 - US); **H01L 21/02598** (2013.01 - KR); **H01L 21/76254** (2013.01 - EP KR US); **H03H 9/02031** (2013.01 - US); **H03H 9/02574** (2013.01 - US); **H03H 9/54** (2013.01 - US); **H03H 9/64** (2013.01 - US); **H10N 30/072** (2023.02 - EP KR US); **H10N 30/076** (2023.02 - KR); **H10N 30/079** (2023.02 - EP KR US); **H10N 30/093** (2023.02 - US); **H10N 30/20** (2023.02 - KR); **H10N 30/8542** (2023.02 - EP US); **H10N 30/87** (2023.02 - KR); **C01G 31/02** (2013.01 - US); **C01G 33/00** (2013.01 - US); **C01G 35/00** (2013.01 - US); **H10N 30/076** (2023.02 - EP US)

Designated contracting state (EPC)

AL AT BE BG CH CY CZ DE DK EE ES FI FR GB GR HR HU IE IS IT LI LT LU LV MC MK MT NL NO PL PT RO RS SE SI SK SM TR

Designated extension state (EPC)

BA ME

DOCDB simple family (publication)

FR 3045677 A1 20170623; **FR 3045677 B1 20190719**; CN 108603305 A 20180928; EP 3394324 A1 20181031; JP 2019508924 A 20190328; JP 6816147 B2 20210120; KR 102681655 B1 20240705; KR 20180098343 A 20180903; SG 11201805382S A 20180730; US 11101428 B2 20210824; US 2018375014 A1 20181227; US 2021367139 A1 20211125; WO 2017108994 A1 20170629

DOCDB simple family (application)

FR 1563055 A 20151222; CN 201680080405 A 20161221; EP 16819558 A 20161221; EP 2016082245 W 20161221; JP 2018532582 A 20161221; KR 20187021267 A 20161221; SG 11201805382S A 20161221; US 201616064416 A 20161221; US 202117396374 A 20210806